Electronic supplementary information

A novel approach of binary doping sulfur and nitrogen into graphene layers for enhancing electrochemical performances in supercapacitors

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Figure S1 N_2 sorption isotherms of NG and S-GIC
**Figure S2** FTIR spectra of RGO and SN-RGO

**Figure S3** (a) XPS survey spectrum and (b) high resolution spectrum of S2p of S-GIC
**Figure S4** CV curves of (a) RGO and (b) SN-RGO at different scan rates ranging from 5 to 500 mV s⁻¹

**Figure S5** Galvanostatic charge/discharge curves of (a) RGO and (b) SN-RGO at various current densities